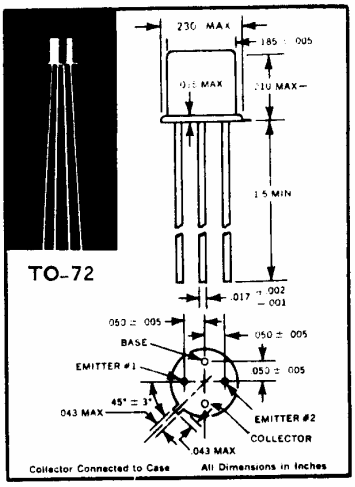
HIGH VOLTAGE
SILICON EPITAXIAL JUNCTION
INTEGRATED CHOPPER TRANSISTOR

3N93
3N94
3N95

- LOW LEAKAGE
- LOW C_{ob}
- LOW r_{EE} (sat)
- HIGH V_{EE} & V_{EB}



ELECTRICAL DATA ABSOLUTE MAXIMUM RATING

PARAMETER	SYMBOL	3N93, 94, 95	UNITS
Collector to Base Voltage	BV_{CBO}	−50	Volts
Emitter (1) to Base Voltage	BV_{E1BO}	−50	Volts
Emitter (2) to Base Voltage	BV_{E2BO}	−50	Volts
Emitter to Emitter Voltage	BV_{E1E2O}	−50	Volts
Emitter (1) to Collector Voltage	BV_{E1CO}	−50	Volts
Emitter (2) to Collector Voltage	BV_{E2CO}	−50	Volts
Power Diss. @ 25 °C Ambient	P_T	300 mW DERATING 1.7 mW/°C	
Junction Temp. (Oper. & Store)	T_J	−65°C to +200°C	
Lead Temp. (@ 1/16" from Case)	T_L	240°C for 10 sec.	

ELECTRICAL CHARACTERISTICS: T_A = 25°C (UNLESS OTHERWISE STATED)

			3N93			3N94			3N95			
PARAMETER	SYMBOL	CONDITION	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	UNITS
Offset Voltage	V_{E1E2O}	I_B = −1.0mA	—	25	50	—	50	100	—	100	200	μV
Offset Voltage	ΔV_{E1E2O}	I_B = −1.0mA TEMP = −25°C to +100°C	—	25	75	—	50	125	—	75	175	μV
Offset Voltage	ΔV_{E1E2O}	ΔI_B = 0.5 to 1.5mA	—	10	25	—	25	50	—	25	75	μV
Saturation Resistance	r_{E1E2}(sat)	I_B = 1.0mA	10	50	75	10	50	75	10	50	100	OHMS
Emitter Cutoff Current	I_{E1BO} I_{E2BO}	V_{EB} = −25V	—	.5	1	—	.5	1	—	.5	1	nA
Emitter Cutoff Current	I_{E1E2O}	V_{EE} = ±25V	—	.5	1	—	.5	1	—	.5	1	nA
Emitter Cutoff Current	I_{E1E2O}	V_{EE} = ±25V TEMP = 100°C	—	50	75	—	50	75	—	50	75	nA
Emitter to Base Capacitance	C_{eb}	V_{EB} = 6V I_C = 0 f = 4MC	—	2	3	—	2	3	—	2	3	pfd
Collector to Base Capacitance	C_{ob}	V_{CB} = −6V f = 4MC I_C = 0	—	6	10	—	6	10	—	6	10	pfd

CRYSTALONICS
2805 Veterans Highway
Suite 14
Ronkonkoma, N.Y. 11779